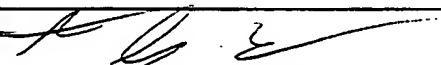


Substitute for form 1449A/PTO			Complete if Known	
			Application Number	10/796,413
			Filing Date	March 10, 2004
			First Named Inventor	Duan
			Art Unit	2891
			Examiner Name	Matthew Reames
Sheet	of		Attorney Docket Number	01-004100

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Examiner Initials	Cite No.	Document No.	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, lines, Where Relevant Passages or Relevant Figures Appeal
		Number - Kind Code (if known)			
M	AA	US-5,714,766	02-03-1998	Chen et al.	
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Examiner Initials	Cite No.	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code - Number - Kind Code (if known)			
M	AS	WO-0103208	01-11-2001	Harvard	
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	AU	WO-0248701	06-20-2002	Harvard	
M	AV	WO-2005017962	02-24-2005	Nanosys	

Examiner Signature		Date Considered	10/26/06
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>		Complete if Known	
		Application Number	10/796,413
		Filing Date	March 10, 2004
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		Art Unit	2891
		Examiner Name	Matthew Reames
Sheet	of	Attorney Docket Number	01-004100

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T
<i>SPJ</i>	AW	ATWATER, H.A. "Silicon nanoparticle engineering for novel logic and memory applications" Project Overview, Functional Nanostructures Program, NSF (January 2001)		
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	BB	CORSO, D. et al., "Localized Charge storage in nanocrystal memories: feasibility of a multi-bit cell" (Publication and Publication date unknown)		
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<i>MM</i>	BJ	VAMPOLA, K. et al., "Growth and Characterization of metal nanocrystals" Cornell Nanofabrication Facility (Publication date unknown)		
	BK			
	BL			

Examiner Signature	<i>SPJ</i>	Date Considered	10/26/00
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